Appl. No. 09/464,297
Amendment dated January 22,2004
Reply to Office Action of October 22, 2003

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

TC 1700

Applicants:

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Appl. No.

09/464,297

Filed:

December 15, 1999

Title

PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A

SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA

AND AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U.

1765

Examiner

Lan Vinh

Docket No.

99-039/RCE

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450

on January 22 2004

(Date of Deposit)

John P. Taylor, Reg. No. 22,369

January 22, 2004

Date of Signature

AMENDMENT

Honorable Commissioner for Patents PO Box 1450 Alexandria, VA 22313-1450

Sir:

Date: January 22, 2004

This is in response to the Sixth Office Action mailed October 22, 2003.